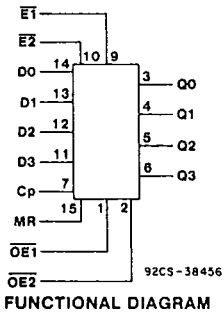


**CD54/74HC173
CD54/74HCT173**

High-Speed CMOS Logic



**Quad D-Type Flip-Flop, 3-State
Positive-Edge Triggered**

Type Features:

- 3-state buffered outputs
- gated input and output enables

The RCA CD54/74HC173 and CD54/74HCT173 high speed 3-STATE QUAD D TYPE FLIP-FLOPS are fabricated with silicon gate CMOS technology. They possess the low power consumption of standard CMOS integrated circuits, and can operate at speeds comparable to the equivalent low power Schottky devices. The buffered outputs can drive 15 LSTTL loads. The large output drive capability and 3-STATE feature make these parts ideally suited for interfacing with bus lines in bus oriented systems.

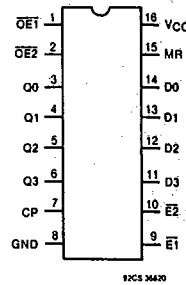
The four D TYPE FLIP-FLOPS operate synchronously from a common clock. The outputs are in the 3-STATE mode when either of the two output disable pins are at the logic "1" level. The input ENABLES allow the flip-flops to remain in their present states without having to disrupt the clock. If either of the 2 input ENABLES are taken to a logic "1" level, the Q outputs are fed back to the inputs, forcing the flip flops to remain in the same state. Reset is enabled by taking the MASTER RESET (MR) input to a logic "1" level. The data outputs change state on the positive going edge of the clock.

The CD54/74HCT173 logic family is functionally as well as pin compatible with the standard 54LS/74LS logic family.

The CD54HC173 and CD54HCT173 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC173 and D74HCT173 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range):
Standard Outputs — 10 LSTTL Loads
Bus Driver Outputs — 15 LSTTL Loads
- Wide Operating Temperature Range:
CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:
2 to 6 V operation
High Noise Immunity: $N_{IL} = 30\%$, $N_{IH} = 30\%$ of V_{CC}
@ $V_{CC} = 5 V$
- CD54HCT/CD74HCT Types:
4.5 to 5.5 V Operation
Direct LSTTL Input Logic Compatibility
 $V_{IL} = 0.8 V \text{ max.}$, $V_{IH} = 2 V \text{ Min.}$
CMOS Input Compatibility
 $I_i \leq 1 \mu A @ V_{OL}, V_{OH}$



TERMINAL ASSIGNMENT

HARRIS SEMICONDUCTOR SECTOR 27E D 4302271 0017639 9 HAS

CD54/74HC173
CD54/74HCT173

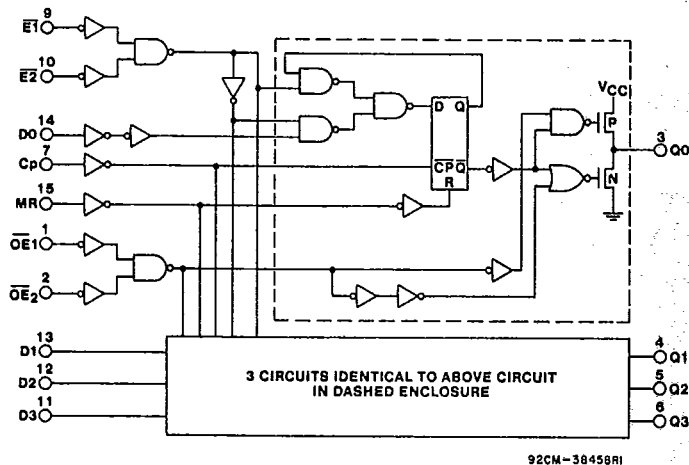
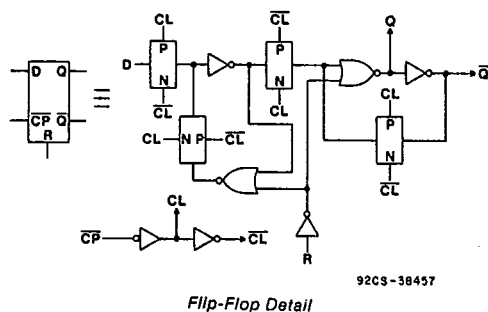


Fig. 1 — Logic diagram for the CD54/74HC/HCT173.



Flip-Flop Detail

TRUTH TABLE

MR	CP	Data Enable		Data	Output Q
		E1	E2	D	
H	X	X	X	X	L
L	L	X	X	X	Q ₀
L	↗	X	H	X	Q ₀
L	↗	L	L	L	L
L	↗	L	L	H	H

When either $\overline{OE1}$ or $\overline{OE2}$ (or both) is (are) high the output is disabled to the high-impedance state, however, sequential operation of the flip-flops is not affected.

H = high level (steady state) X = don't care (any input including transitions)
 L = low level (steady state) Q₀ = the level of Q before the indicated steady-state
 ↗ = low-to-high level transition input conditions were established.

HARRIS SEMICONDUCTOR SECTOR 27E D 430227J 0017640 5 HAS

CD54/74HC173
CD54/74HCT173

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE (V_{CC}):
(Voltages referenced to ground) -0.5 to +7 V

DC INPUT DIODE CURRENT, I_{IK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V) ± 20 mA

DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_o < -0.5$ V OR $V_o > V_{CC} + 0.5$ V) ± 20 mA

DC DRAIN CURRENT, PER OUTPUT (I_o) (FOR -0.5 V $< V_o < V_{CC} + 0.5$ V) ± 35 mA

DC V_{CC} OR GROUND CURRENT (I_{CC}) ± 70 mA

POWER DISSIPATION PER PACKAGE (P_D):

For $T_A = -40$ to $+60^\circ\text{C}$ (PACKAGE TYPE E) 500 mW

For $T_A = +60$ to $+85^\circ\text{C}$ (PACKAGE TYPE E) Derate Linearly at 8 mW/ $^\circ\text{C}$ to 300 mW

For $T_A = -55$ to $+100^\circ\text{C}$ (PACKAGE TYPE F, H) 500 mW

For $T_A = +100$ to $+125^\circ\text{C}$ (PACKAGE TYPE F, H) Derate Linearly at 8 mW/ $^\circ\text{C}$ to 300 mW

For $T_A = -40$ to $+70^\circ\text{C}$ (PACKAGE TYPE M) 400 mW

For $T_A = +70$ to $+125^\circ\text{C}$ (PACKAGE TYPE M) Derate Linearly at 6 mW/ $^\circ\text{C}$ to 70 mW

OPERATING-TEMPERATURE RANGE (T_A):

PACKAGE TYPE F, H -55 to $+125^\circ\text{C}$

PACKAGE TYPE E, M -40 to $+85^\circ\text{C}$

STORAGE TEMPERATURE (T_{stg}) -65 to $+150^\circ\text{C}$

LEAD TEMPERATURE (DURING SOLDERING):

At distance $1/16 \pm 1/32$ in. (1.59 ± 0.79 mm) from case for 10 s max. $+265^\circ\text{C}$

Unit inserted into a PC Board (min. thickness $1/16$ in., 1.59 mm) with solder contacting lead tips only $+300^\circ\text{C}$

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For $T_A =$ Full Package Temperature Range) V_{CC} .*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V_i, V_o	0	V_{CC}	V
Operating Temperature T_A :			
CD74 Types	-40	+85	$^\circ\text{C}$
CD54 Types	-55	+125	$^\circ\text{C}$
Input Rise and Fall Times, t_r, t_f			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

*Unless otherwise specified, all voltages are referenced to Ground.

HARRIS SEMICONDUCTOR SECTOR 27E D 430227J 001764J 7 HAS

CD54/74HC173
CD54/74HCT173

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CD74HC173/CD54HC173										CD74HCT173/CD54HCT173										UNITS			
	TEST CONDITIONS			74HC/54HC TYPE			74HC TYPE			54HC TYPE			TEST CONDITIONS		74HCT/54HCT TYPE			74HCT TYPE				54HCT TYPE		
	V _I V	I _O mA	V _{CC} V	+25°C			-40/ +85°C			-55/ +125°C			V _I V	V _{CC} V	+25°C			-40/ +85°C				-55/ +125°C		
				Min	Typ	Max	Min	Max	Min	Max	Min	Max			Min	Typ	Max	Min	Max	Min		Max		
High-Level Input Voltage V _{IH}			2	1.5	—	—	1.5	—	1.5	—	—	—	4.5		2	—	—	2	—	2	—	V		
			4.5	3.15	—	—	3.15	—	3.15	—	—	—	to											
			6	4.2	—	—	4.2	—	4.2	—	—	—	5.5											
Low-Level Input Voltage V _{IL}			2	—	—	0.5	—	0.5	—	0.5	—	—	4.5		—	—	0.8	—	0.8	—	0.8	V		
			4.5	—	—	1.35	—	1.35	—	1.35	—	—	to											
			6	—	—	1.8	—	1.8	—	1.8	—	—	5.5											
High-Level Output Voltage V _{OH}	V _{IL}		2	1.9	—	—	1.9	—	1.9	—	—	V _{IL}										V		
or		-0.02	4.5	4.4	—	—	4.4	—	4.4	—	—	or	4.5	4.4	—	—	4.4	—	4.4	—	—			
CMOS Loads	V _{IH}		6	5.9	—	—	5.9	—	5.9	—	—	V _{IH}												
TTL Loads (Bus Driver)	V _{IL}											V _{IL}										V		
or		-6	4.5	3.98	—	—	3.84	—	3.7	—	—	or	4.5	3.98	—	—	3.84	—	3.7	—	—			
V _{IH}		-7.8	6	5.48	—	—	5.34	—	5.2	—	—	V _{IH}												
Low-Level Output Voltage V _{OL}	V _{IL}		2	—	—	0.1	—	0.1	—	0.1	—	V _{IL}										V		
or		0.02	4.5	—	—	0.1	—	0.1	—	0.1	—	or	4.5	—	—	0.1	—	0.1	—	0.1	—			
CMOS Loads	V _{IH}		6	—	—	0.1	—	0.1	—	0.1	—	V _{IH}												
TTL Loads (Bus Driver)	V _{IL}											V _{IL}										V		
or		6	4.5	—	—	0.26	—	0.33	—	0.4	—	or	4.5	—	—	0.26	—	0.33	—	0.4	—			
V _{IH}		7.8	6	—	—	0.26	—	0.33	—	0.4	—	V _{IH}												
Input Leakage Current I _I	V _{CC}		6	—	—	±0.1	—	±1	—	±1	—	Any Voltage Between V _{CC} & Gnd	5.5	—	—	±0.1	—	±1	—	±1	—	μA		
or																								
Gnd																								
Quiescent Device Current I _{CC}	V _{CC}		0	6	—	—	8	—	80	—	160	V _{CC}	5.5	—	—	8	—	80	—	160	—	μA		
or												or												
Gnd												Gnd												
Additional Quiescent Device Current per input pin: 1 unit load ΔI _{CC} *												V _{CC} -2.1	4.5 to 5.5	—	100	360	—	450	—	490	—	μA		
3-State Leakage Current I _{OZ}	V _{IL} or V _{IH}	V _O =V _{CC} or Gnd	6	—	—	±0.5	—	±5.0	—	±10	—	V _{IL} or V _{IH}	5.5	—	—	±0.5	—	±5.0	—	±10	—	μA		

*For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
D0-D3	0.15
E1 & E2	0.15
CP	0.25
MR	0.2
OE1 & OE2	0.5

*Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25°C.

HARRIS SEMICONDUCTOR 27E D 4302271 0017642 9 HAS

CD54/74HC173
CD54/74HCT173

SWITCHING CHARACTERISTICS ($V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$, Input $t_r, t_f = 6\text{ ns}$)

CHARACTERISTIC	C_L (pF)	TYPICAL		UNITS	
		HC	HCT		
Propagation Delay, Clock to Q	t_{PLH} t_{PHL}	15	17	18	ns
Propagation Delay, Output Disable and Enable to Q	t_{PLZ} t_{PHZ} t_{PZL} t_{PZH}	15	12	12	ns
Maximum Clock Frequency	f_{max}	—	60	60	MHz
Power Dissipation Capacitance*	C_{PD}	—	29	34	pF

* C_{PD} is used to determine the dynamic power consumption, per package.
 $P_D = C_{PD} V_{CC}^2 f_i + \sum C_L V_{CC}^2 f_o$ where: f_i = input frequency, f_o = output frequency,
 C_L = output load capacitance, V_{CC} = supply voltage.

PREREQUISITE FOR SWITCHING FUNCTION

CHARACTERISTIC	TEST CONDITION V_{CC} V	LIMITS												UNITS
		25°C				-40°C to +85°C				-55°C to +125°C				
		HC		HCT		74HC		74HCT		54HC		54HCT		
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Maximum Clock Frequency f_{max} Fig. 3	2	6	—	—	5	—	—	—	4	—	—	—	MHz	
	4.5	30	20	—	24	16	—	—	20	13	—	—		
	6	35	—	—	28	—	—	—	24	—	—	—		
MR Pulse Width t_w Fig. 4	2	80	—	—	100	—	—	—	120	—	—	—	ns	
	4.5	16	15	—	20	19	—	—	24	22	—	—		
	6	14	—	—	17	—	—	—	20	—	—	—		
Clock Pulse Width t_w Fig. 3	2	80	—	—	100	—	—	—	120	—	—	—	ns	
	4.5	16	25	—	20	31	—	—	24	38	—	—		
	6	14	—	—	17	—	—	—	20	—	—	—		
Set-up Time Data to Clock Fig. 5 t_{SU}	2	60	—	—	75	—	—	—	90	—	—	—	ns	
	4.5	12	12	—	15	15	—	—	18	18	—	—		
	6	10	—	—	13	—	—	—	15	—	—	—		
Set-up Time \bar{E} to Clock t_{SU}	2	60	—	—	75	—	—	—	90	—	—	—	ns	
	4.5	12	18	—	15	23	—	—	18	27	—	—		
	6	10	—	—	13	—	—	—	15	—	—	—		
Hold Time Data to Clock Fig. 5 t_H	2	3	—	—	3	—	—	—	3	—	—	—	ns	
	4.5	3	0	—	3	0	—	—	3	0	—	—		
	6	3	—	—	3	—	—	—	3	—	—	—		
Hold Time \bar{E} to Clock t_H	2	0	—	—	0	—	—	—	0	—	—	—	ns	
	4.5	0	0	—	0	0	—	—	0	0	—	—		
	6	0	—	—	0	—	—	—	0	—	—	—		
Removal Time MR to Clock t_{REM}	2	60	—	—	75	—	—	—	90	—	—	—	ns	
	4.5	12	12	—	15	15	—	—	18	18	—	—		
	6	10	—	—	13	—	—	—	15	—	—	—		

HARRIS SEMICONDUCTOR 27E D 4302271 0017643 0 HAS

CD54/74HC173
CD54/74HCT173

SWITCHING CHARACTERISTICS ($V_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

CHARACTERISTIC	TEST CONDITION	LIMITS												UNITS	
		25°C				-40°C to +85°C				-55°C to +125°C					
		HC		HCT		74HC		74HCT		54HC		54HCT			
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
Propagation Delay Clock to Output Fig. 3	t_{PLH}	2	—	200	—	—	—	250	—	—	—	300	—	—	ns
	t_{PHL}	4.5	—	40	—	43	—	50	—	54	—	60	—	65	
		6	—	34	—	—	—	43	—	—	—	51	—	—	
Propagation Delay MR to Output Fig. 4	t_{PHL}	2	—	175	—	—	—	220	—	—	—	265	—	—	ns
		4.5	—	35	—	37	—	44	—	46	—	53	—	56	
		6	—	30	—	—	—	37	—	—	—	45	—	—	
Propagation Delay, Output Enable to Q t_{PHZ}	t_{PLZ}	2	—	150	—	—	—	190	—	—	—	225	—	—	ns
	t_{PHZ}	4.5	—	30	—	30	—	38	—	38	—	45	—	45	
		6	—	26	—	—	—	33	—	—	—	38	—	—	
		2	—	150	—	—	—	190	—	—	—	225	—	—	ns
		4.5	—	30	—	35	—	38	—	44	—	45	—	53	
		6	—	26	—	—	—	33	—	—	—	38	—	—	
Output Transition Time Fig. 3	t_{TLH}	2	—	60	—	—	—	75	—	—	—	90	—	—	ns
	t_{THL}	4.5	—	12	—	12	—	15	—	15	—	18	—	18	
		6	—	10	—	—	—	13	—	—	—	15	—	—	
Input Capacitance	C_i	—	—	10	—	10	—	10	—	10	—	10	—	10	pF
3-State Output Capacitance	C_o	—	—	20	—	20	—	20	—	20	—	20	—	20	pF

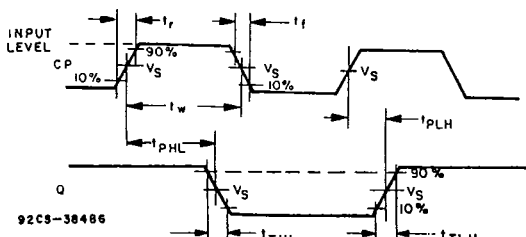


Fig. 3 — Clock to output delays and clock pulse width.

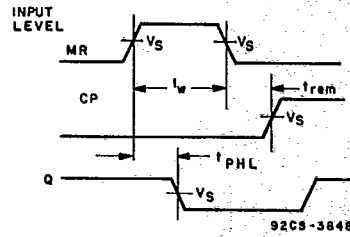


Fig. 4 — Master reset pulse width, Master reset to output delay and master reset to clock recovery time.

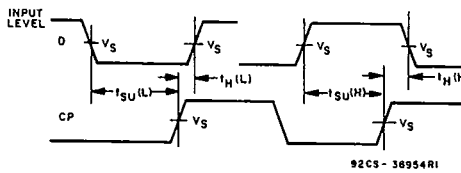


Fig. 5 — Data set-up and hold times.

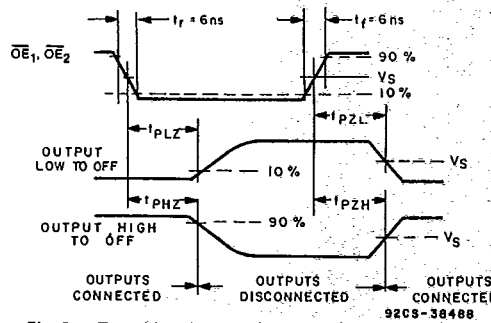


Fig. 6 — Transition times and propagation delay times.

	CD54/74HC	CD54/74HCT
Input Level	V_{CC}	3 V
V_S	$0.5 V_{CC}$	1.3 V

HARRIS SEMICONDUCTOR 27E D 430227J 0017644 2 HAS